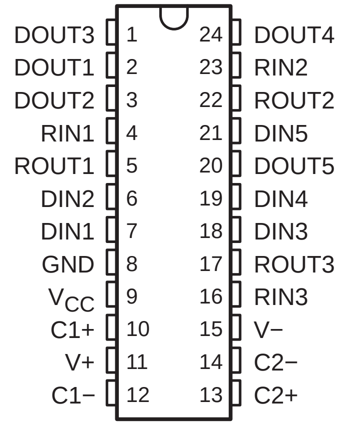
- **ESD Protection for RS-232 I/O Pins**
  - **±15 kV − Human-Body Model**
- **Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards**
- **Operates at 5-V V_{CC} Supply**
- **Operates Up To 120 kbit/s**
- **External Capacitors . . . 4 × 0.1 μF**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **Applications**
  - **Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment**

DB OR DW PACKAGE
(TOP VIEW)



description/ordering information

The MAX207 consists of five line drivers, three line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 5-V supply. The devices operate at data signaling rates up to 120 kbit/s and a maximum of 30-V/μs driver output slew rate.

ORDERING INFORMATION

T_A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
0°C to 70°C	SOIC (DW)	Tube of 25	MAX207CDW	MAX207C
		Reel of 2000	MAX207CDWR	
	SSOP (DB)	Reel of 2000	MAX207CDBR	MA207C
−40°C to 85°C	SOIC (DW)	Tube of 25	MAX207IDW	MAX207I
		Reel of 2000	MAX207IDWR	
	SSOP (DB)	Reel of 2000	MAX207IDBR	MB207I

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

Function Tables

EACH DRIVER

INPUT D_{IN}	OUTPUT D_{OUT}
L	H
H	L

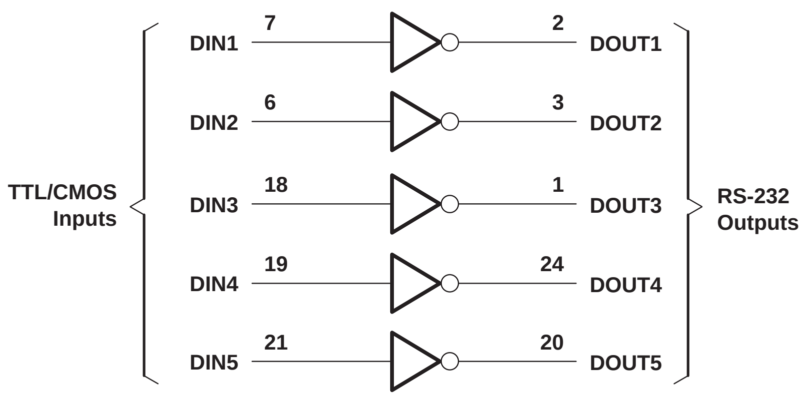
H = high level, L = low level

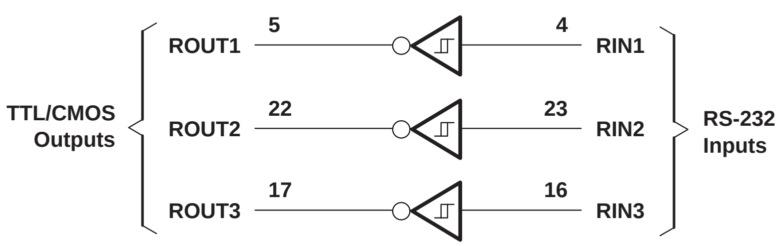
EACH RECEIVER

INPUT R_{IN}	OUTPUT R_{OUT}
L	H
H	L
Open	H

H = high level, L = low level, Open = input disconnected or connected driver off

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} (see Note 1)	−0.3 V to 6 V
Positive charge pump voltage range, V+ (see Note 1)	V_{CC} − 0.3 V to 14 V
Negative charge pump voltage range, V− (see Note 1)	−14 V to 0.3 V
Input voltage range, V_I: Drivers	−0.3 V to V+ + 0.3 V
Input voltage range, V_I: Receivers	±30 V
Output voltage range, V_O: Drivers	V− − 0.3 V to V+ + 0.3 V
Output voltage range, V_O: Receivers	−0.3 V to V_{CC} + 0.3 V
Short-circuit duration: D_{OUT}	Continuous
Package thermal impedance, θ_{JA} (see Notes 2 and 3): DB package	63°C/W
Package thermal impedance, θ_{JA} (see Notes 2 and 3): DW package	46°C/W
Operating virtual junction temperature, T_J	150°C
Storage temperature range, T_{stg}	−65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.
2. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4 and Figure 4)

			MIN	NOM	MAX	UNIT
	Supply voltage		4.5	5	5.5	V
V_{IH}	Driver high-level input voltage	D_{IN}	2			V
V_{IL}	Driver low-level input voltage	D_{IN}			0.8	V
V_I	Driver input voltage	D_{IN}	0		5.5	V
V_I	Receiver input voltage		−30		30	V
T_A	Operating free-air temperature	MAX207C	0		70	°C
T_A	Operating free-air temperature	MAX207I	−40		85	°C

NOTE 4: Test conditions are C1−C4 = 0.1 μF at V_{CC} = 5 V ± 0.5 V.

electrical characteristics over recommended ranges of supply voltage (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{CC}	Supply current	No load, V_{CC} = 5 V, T_A = 25°C		11	20	mA

NOTE 4: Test conditions are C1−C4 = 0.1 μF at V_{CC} = 5 V ± 0.5 V.

DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	D_{OUT} at R_L = 3 kΩ to GND,	D_{IN} = GND	5	9		V
V_{OL}	Low-level output voltage	D_{OUT} at R_L = 3 kΩ to GND,	D_{IN} = V_{CC}	−5	−9		V
I_{IH}	High-level input current	V_I = V_{CC}			15	200	μA
I_{IL}	Low-level input current	V_I at 0 V			−15	−200	μA
I_{OS}‡	Short-circuit output current	V_{CC} = 5.5 V,	V_O = 0 V		±10	±60	mA
r_o	Output resistance	V_{CC}, V+, and V− = 0 V,	V_O = ±2 V	300			Ω

† All typical values are at V_{CC} = 5 V, and T_A = 25°C.
‡ Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.
NOTE 4: Test conditions are C1−C4 = 0.1 μF at V_{CC} = 5 V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
	Maximum data rate	C_L = 50 to 1000 pF, One D_{OUT} switching,	R_L = 3 kΩ to 7 kΩ, See Figure 1	120			kbit/s
$t_{PLH (D)}$	Propagation delay time, low- to high-level output	C_L = 2500 pF, all drivers loaded,	R_L = 3 kΩ, See Figure 1		2		μs
$t_{PHL (D)}$	Propagation delay time, high- to low-level output	C_L = 2500 pF, all drivers loaded,	R_L = 3 kΩ, See Figure 1		2		μs
$t_{sk(p)}$	Pulse skew§	C_L = 150 pF to 2500 pF,	R_L = 3 kΩ to 7 kΩ, See Figure 2		300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	C_L = 50 pF to 1000 pF V_{CC} = 5 V	R_L = 3 kΩ to 7 kΩ,	3	6	30	V/μs

† All typical values are at V_{CC} = 5 V, and T_A = 25°C.
§ Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
NOTE 4: Test conditions are C1−C4 = 0.1 μF at V_{CC} = 5 V ± 0.5 V.

ESD protection

PIN	TEST CONDITIONS	TYP	UNIT
D_{OUT}, R_{IN}	Human-Body Model	±15	kV

RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = −1 mA		3.5	V_{CC}−0.4 V		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA				0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 5 V,	T_A = 25°C		1.7	2.4	V
V_{IT-}	Negative-going input threshold voltage	V_{CC} = 5 V,	T_A = 25°C	0.8	1.2		V
V_{hys}	Input hysteresis (V_{IT+} − V_{IT-})			0.2	0.5	1	V
r_i	Input resistance	V_I = ±3 V to ±25 V		3	5	7	kΩ

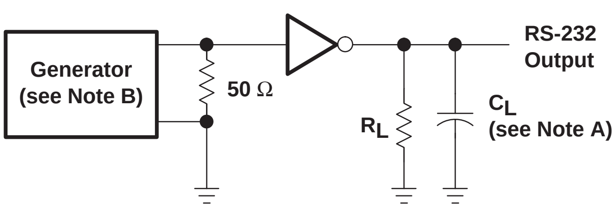
† All typical values are at V_{CC} = 5 V, and T_A = 25°C.
NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 5 V ± 0.5 V.

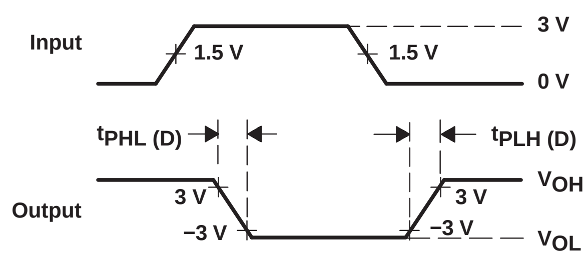
switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 3)

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L= 150 pF		0.5	10	µs
t_{PHL}	Propagation delay time, high- to low-level output			0.5	10	µs
$t_{sk(p)}$	Pulse skew‡			300		ns

† All typical values are at V_{CC} = 5 V, and T_A = 25°C.
‡ Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
NOTE 4: Test conditions are C1−C4 = 0.1 µF, at V_{CC} = 5 V ± 0.5 V.

PARAMETER MEASUREMENT INFORMATION



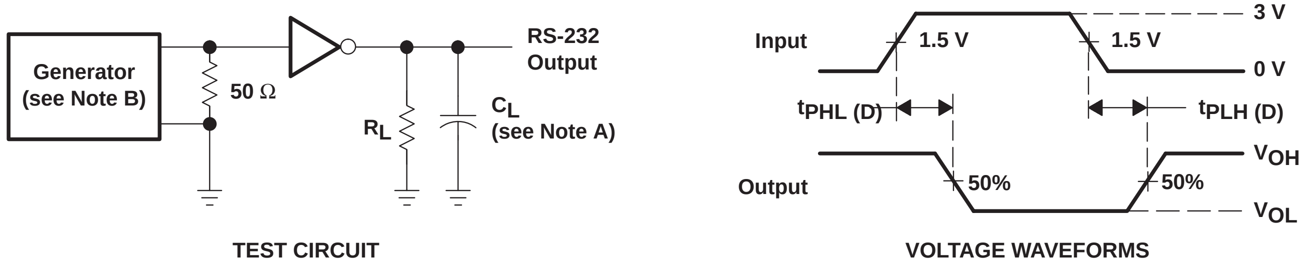


$$SR(tr) = \frac{6\ V}{t_{PHL\ (D)}\ \text{or}\ t_{PLH\ (D)}}$$

NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 120 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

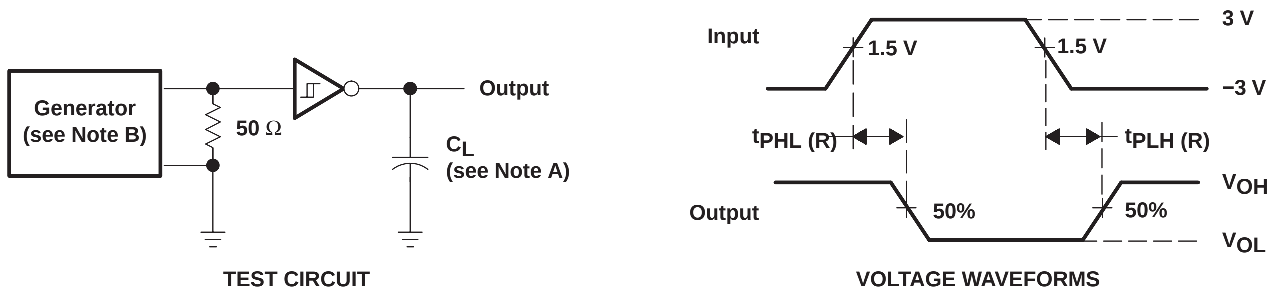
Figure 1. Driver Slew Rate

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 120 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \leq$ 10 ns, $t_f \leq$ 10 ns.

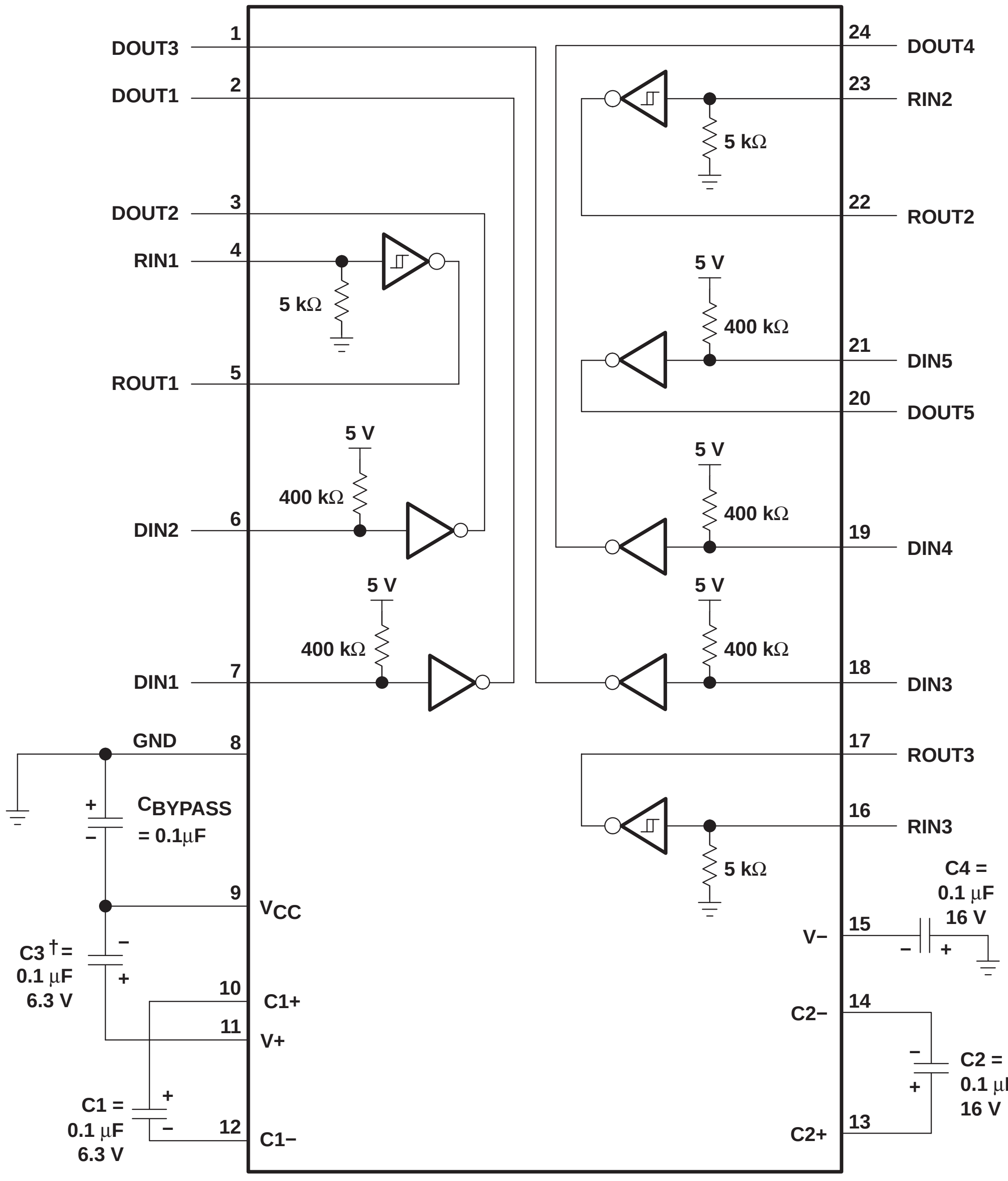
Figure 2. Driver Pulse Skew



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \leq$ 10 ns, $t_f \leq$ 10 ns.

Figure 3. Receiver Propagation Delay Times

APPLICATION INFORMATION



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

Figure 4. Typical Operating Circuit and Capacitor Values

APPLICATION INFORMATION

capacitor selection

The capacitor type used for C1−C4 is not critical for proper operation. The MAX207 requires 0.1-µF capacitors, although capacitors up to 10 µF can be used without harm. Ceramic dielectrics are suggested for the 0.1-µF capacitors. When using the minimum recommended capacitor values, make sure the capacitance value does not degrade excessively as the operating temperature varies. If in doubt, use capacitors with a larger (e.g., 2×) nominal value. The capacitors' effective series resistance (ESR), which usually rises at low temperatures, influences the amount of ripple on V+ and V−.

Use larger capacitors (up to 10 µF) to reduce the output impedance at V+ and V−.

Bypass V_{CC} to ground with at least 0.1 µF. In applications sensitive to power-supply noise generated by the charge pumps, decouple V_{CC} to ground with a capacitor the same size as (or larger than) the charge-pump capacitors (C1−C4).

ESD protection

TI MAX207 devices have standard ESD protection structures incorporated on the pins to protect against electrostatic discharges encountered during assembly and handling. In addition, the RS232 bus pins (driver outputs and receiver inputs) of these devices have an extra level of ESD protection. Advanced ESD structures were designed to successfully protect these bus pins against ESD discharge of ±15-kV when powered down.

ESD test conditions

ESD testing is stringently performed by TI, based on various conditions and procedures. Please contact TI for a reliability report that documents test setup, methodology, and results.

Human-Body Model

The Human-Body Model (HBM) of ESD testing is shown in Figure 5, while Figure 6 shows the current waveform that is generated during a discharge into a low impedance. The model consists of a 100-pF capacitor, charged to the ESD voltage of concern, and subsequently discharged into the device under test (DUT) through a 1.5-kΩ resistor.

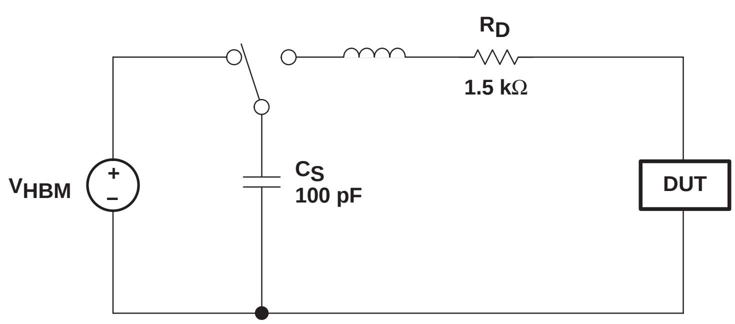


Figure 5. HBM ESD Test Circuit

APPLICATION INFORMATION

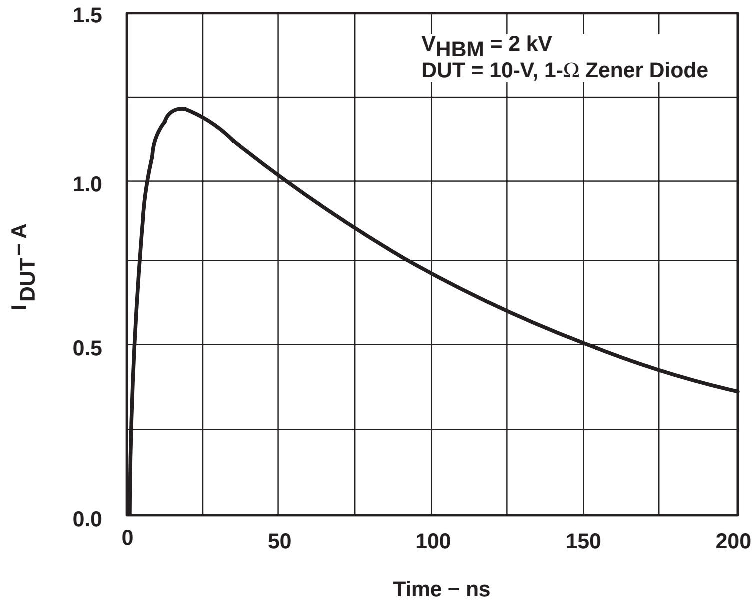


Figure 6. Typical HBM Current Waveform

Machine Model

The Machine Model (MM) ESD test applies to all pins using a 200-pF capacitor with no discharge resistance. The purpose of the MM test is to simulate possible ESD conditions that can occur during the handling and assembly processes of manufacturing. In this case, ESD protection is required for all pins, not just RS-232 pins. However, after PC board assembly, the MM test no longer is as pertinent to the RS-232 pins.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
MAX207CDB	Obsolete	Production	SSOP (DB) | 24	-	-	Call TI	Call TI	0 to 70	MA207C
MAX207CDBR	Active	Production	SSOP (DB) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MA207C
MAX207CDBR.A	Active	Production	SSOP (DB) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MA207C
MAX207CDW	Obsolete	Production	SOIC (DW) | 24	-	-	Call TI	Call TI	0 to 70	MAX207C
MAX207CDWR	Obsolete	Production	SOIC (DW) | 24	-	-	Call TI	Call TI	0 to 70	MAX207C
MAX207IDBR	Active	Production	SSOP (DB) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MB207I
MAX207IDBR.A	Active	Production	SSOP (DB) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MB207I
MAX207IDW	Obsolete	Production	SOIC (DW) | 24	-	-	Call TI	Call TI	-40 to 85	MAX207I
MAX207IDWR	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX207I
MAX207IDWR.A	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX207I

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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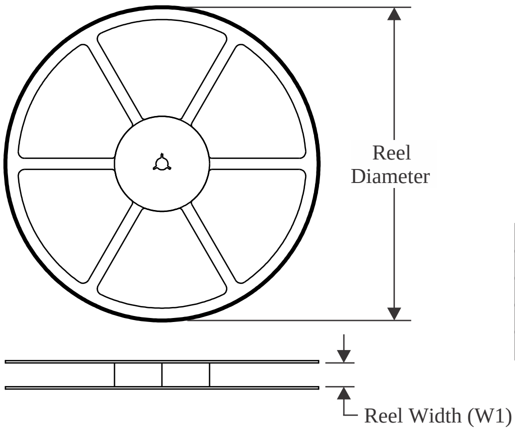
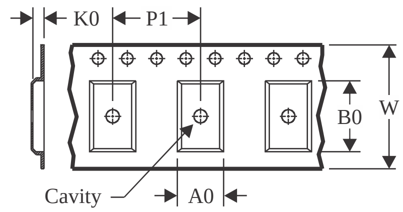
TAPE AND REEL INFORMATION

REEL DIMENSIONS

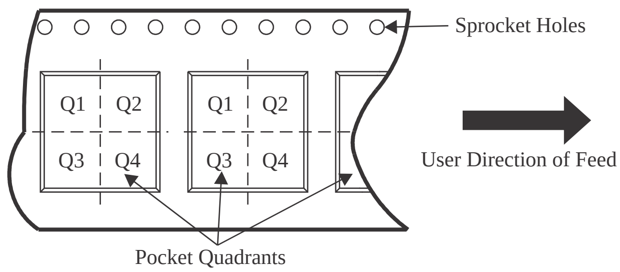


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

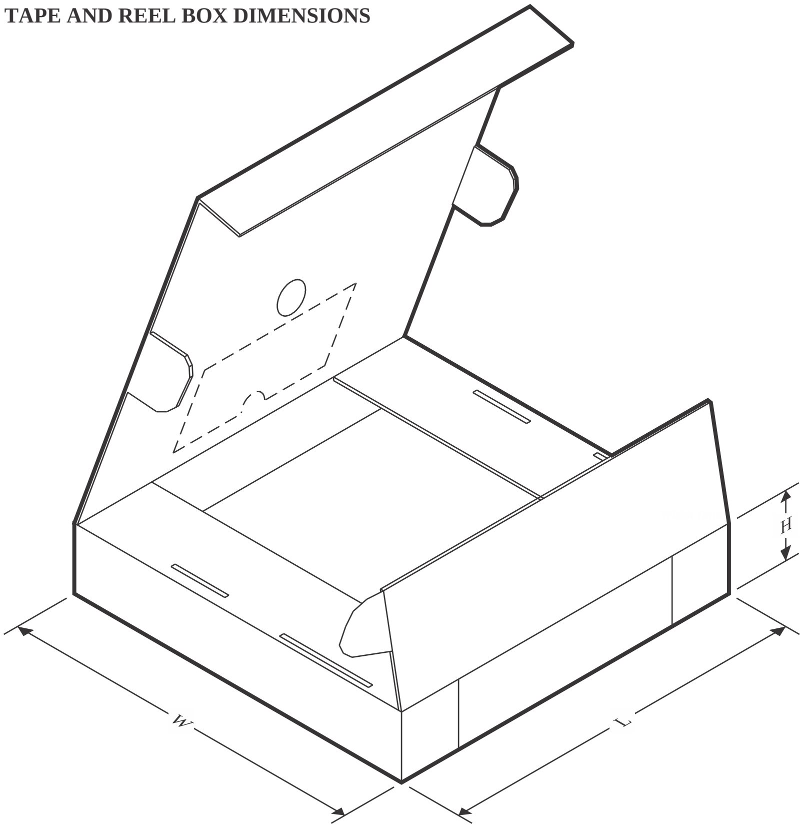
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
MAX207CDBR	SSOP	DB	24	2000	330.0	16.4	8.2	8.8	2.5	12.0	16.0	Q1
MAX207IDBR	SSOP	DB	24	2000	330.0	16.4	8.2	8.8	2.5	12.0	16.0	Q1
MAX207IDWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1

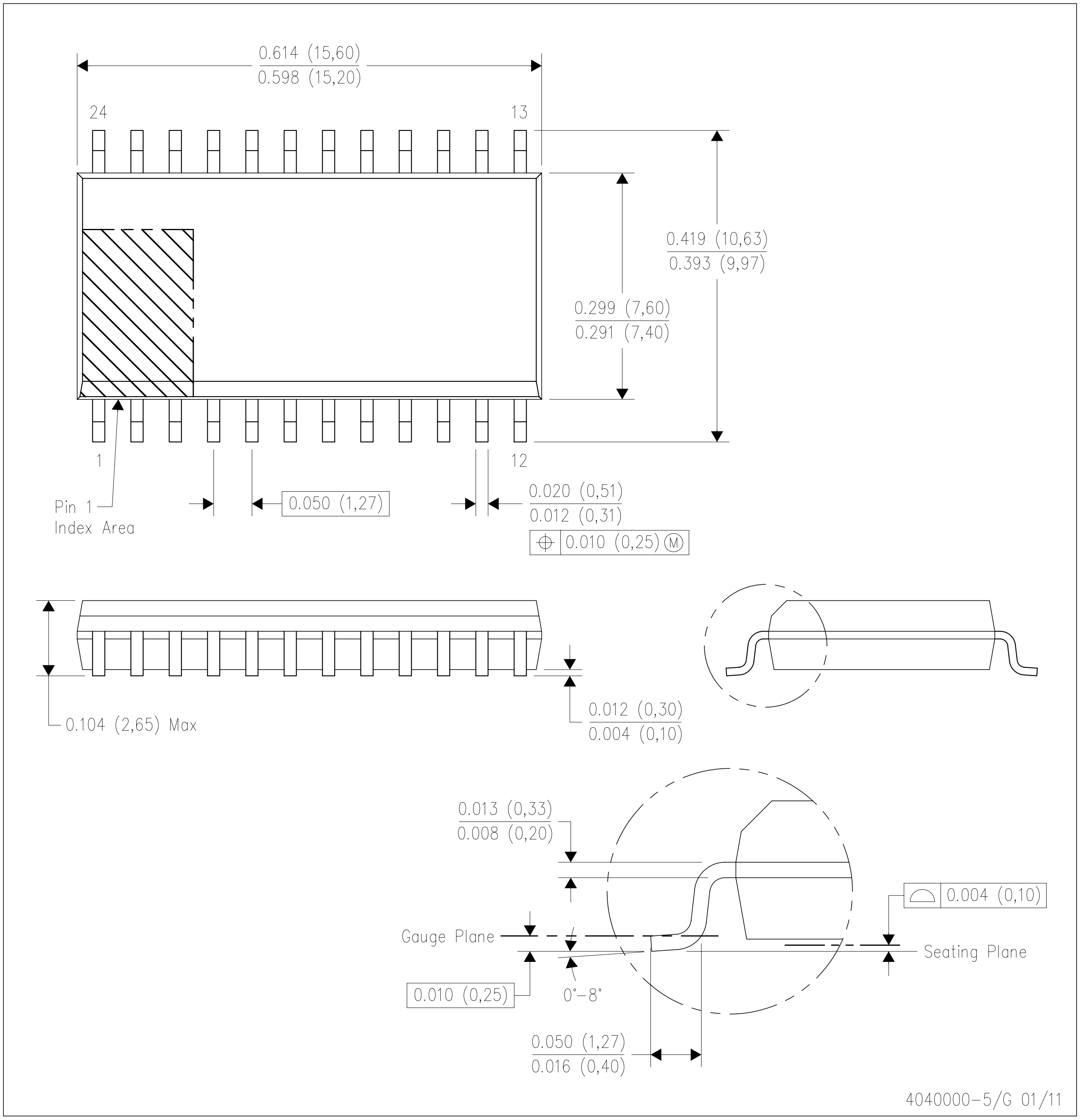
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
MAX207CDBR	SSOP	DB	24	2000	356.0	356.0	35.0
MAX207IDBR	SSOP	DB	24	2000	356.0	356.0	35.0
MAX207IDWR	SOIC	DW	24	2000	350.0	350.0	43.0

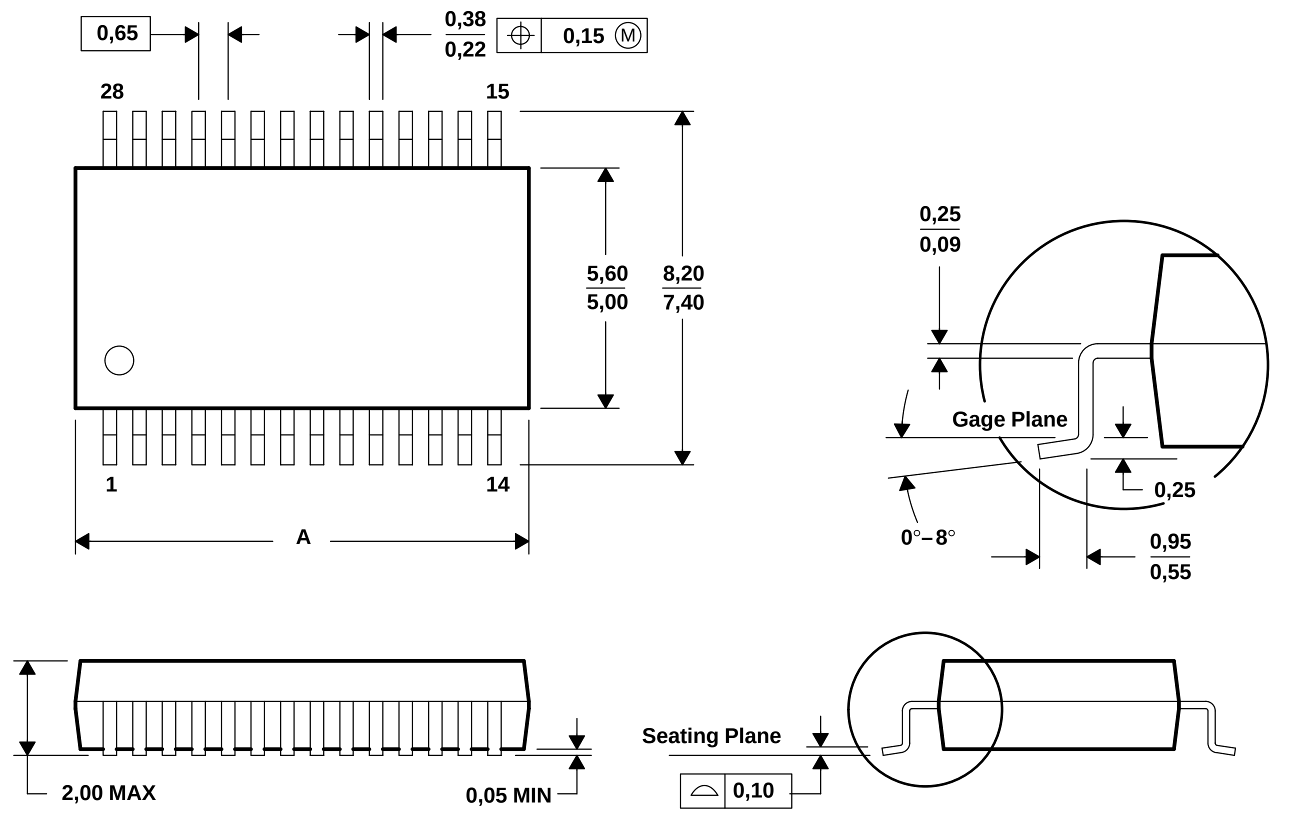
DW (R-PDSO-G24) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS-013 variation AD.

DB (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

28 PINS SHOWN



DIM \ PINS **	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

4040065 /E 12/01

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150

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